## MC100LVEL11

### 3.3V ECL 1:2 Differential Fanout Buffer

## Description

The MC100LVEL11 is a differential 1:2 fanout buffer. The device is functionally similar to the E111 device but with higher performance capabilities. Having within-device skews and output transition times significantly improved over the E111, the LVEL11 is ideally suited for those applications which require the ultimate in AC performance.

The differential inputs of the LVEL11 employ clamping circuitry to maintain stability under open input conditions. If the inputs are left open (pulled to $\mathrm{V}_{\mathrm{EE}}$ ) the Q outputs will go LOW.

## Features

- 330 ps Propagation Delay
- 5 ps Skew Between Outputs
- High Bandwidth Output Transitions
- The 100 Series Contains Temperature Compensation
- PECL Mode Operating Range: $\mathrm{V}_{\mathrm{CC}}=3.0 \mathrm{~V}$ to 3.8 V with $\mathrm{V}_{\mathrm{EE}}=0 \mathrm{~V}$
- NECL Mode Operating Range: $\mathrm{V}_{\mathrm{CC}}=0 \mathrm{~V}$ with $\mathrm{V}_{\mathrm{EE}}=-3.0 \mathrm{~V}$ to -3.8 V
- Internal Input Pulldown Resistors on D, Pullup and Pulldown Resistors on $\overline{\mathrm{D}}$
- Q Output will Default LOW with Inputs Open or at $\mathrm{V}_{\mathrm{EE}}$
- These Devices are $\mathrm{Pb}-$ Free and are RoHS Compliant


Figure 1. Logic Diagram and Pinout Assignment

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ORDERING INFORMATION
See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

## MC100LVEL11

Table 1. PIN DESCRIPTION

| Pin | Function |
| :---: | :--- |
| Q0, $\overline{\text { Q0; Q1, Q1 }}$ | ECL Data Outputs |
| $\mathrm{D}, \overline{\mathrm{D}}$ | ECL Data Inputs |
| $\mathrm{V}_{\mathrm{CC}}$ | Positive Supply |
| $\mathrm{V}_{\mathrm{EE}}$ | Negative Supply |
| EP | (DFN8 only) Thermal exposed pad must be connected to a suffi- <br> cient thermal conduit. Electrically connect to the most negative <br> supply (GND) or leave unconnected, floating open. |

Table 2. ATTRIBUTES

| Characteristics | Value |
| :--- | :---: |
| Internal Input Pulldown Resistor | $\begin{array}{rl}75 \mathrm{k} \Omega\end{array}$ |
| Internal Input Pullup Resistor | $\begin{array}{r}\text { Human Body Model } \\ \text { Machine Model } \\ \text { Charge Device Model }\end{array}$ | \(\left.\begin{array}{r}75 \mathrm{k} \Omega <br>

\hline ESD Protection <br>
\hline Moisture Sensitivity, Indefinite Time Out of Drypack (Note 1) <br>
SOIC-8 <br>
TSSOP-8 <br>
DFN8\end{array}\right)\)

1. For additional information, see Application Note AND8003/D.

Table 3. MAXIMUM RATINGS

| Symbol | Parameter | Condition 1 | Condition 2 | Rating | Units |
| :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{V}_{\mathrm{CC}}$ | PECL Mode Power Supply | $\mathrm{V}_{\mathrm{EE}}=0 \mathrm{~V}$ |  | 8 to 0 | V |
| $\mathrm{V}_{\mathrm{EE}}$ | NECL Mode Power Supply | $\mathrm{V}_{\mathrm{CC}}=0 \mathrm{~V}$ |  | -8 to 0 | V |
| $\mathrm{V}_{1}$ | PECL Mode Input Voltage NECL Mode Input Voltage | $\begin{aligned} & \mathrm{V}_{\mathrm{EE}}=0 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{CC}}=0 \mathrm{~V} \end{aligned}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{I}} \leq \mathrm{V}_{\mathrm{CC}} \\ & \mathrm{~V}_{\mathrm{I}} \geq \mathrm{V}_{\mathrm{EE}} \end{aligned}$ | 6 to 0 -6 to 0 | V |
| $\mathrm{I}_{\text {out }}$ | Output Current | Continuous Surge |  | $\begin{gathered} 50 \\ 100 \end{gathered}$ | $\begin{aligned} & \mathrm{mA} \\ & \mathrm{~mA} \end{aligned}$ |
| $\mathrm{T}_{\mathrm{A}}$ | Operating Temperature Range |  |  | -40 to +95 | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\text {stg }}$ | Storage Temperature Range |  |  | -65 to +150 | ${ }^{\circ} \mathrm{C}$ |
| $\theta_{\mathrm{JA}}$ | Thermal Resistance (Junction-to-Ambient) | $\begin{aligned} & 0 \mathrm{lpfm} \\ & 500 \mathrm{lpfm} \end{aligned}$ | $\begin{aligned} & \text { SOIC-8 } \\ & \text { SOIC-8 } \end{aligned}$ | $\begin{aligned} & 190 \\ & 130 \end{aligned}$ | $\begin{aligned} & \hline{ }^{\circ} \mathrm{C} / \mathrm{W} \\ & { }^{\circ} \mathrm{C} / \mathrm{W} \end{aligned}$ |
| $\theta_{\text {Jc }}$ | Thermal Resistance (Junction-to-Case) | Standard Board | SOIC-8 | 41 to $44 \pm 5 \%$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\theta_{\mathrm{JA}}$ | Thermal Resistance (Junction-to-Ambient) | 0 lpfm 500 lpfm | $\begin{aligned} & \text { TSSOP-8 } \\ & \text { TSSOP-8 } \end{aligned}$ | $\begin{aligned} & 185 \\ & 140 \end{aligned}$ | $\begin{aligned} & \hline{ }^{\circ} \mathrm{C} / \mathrm{W} \\ & { }^{\circ} \mathrm{C} / \mathrm{W} \end{aligned}$ |
| $\theta_{\text {JC }}$ | Thermal Resistance (Junction-to-Case) | Standard Board | TSSOP-8 | 41 to $44 \pm 5 \%$ | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| $\theta_{\mathrm{JA}}$ | Thermal Resistance (Junction-to-Ambient) | 0 lfpm 500 lfpm | DFN8 DFN8 | $\begin{gathered} 129 \\ 84 \end{gathered}$ | $\begin{aligned} & { }^{\circ} \mathrm{C} / \mathrm{W} \\ & { }^{\circ} \mathrm{C} / \mathrm{W} \end{aligned}$ |
| $\mathrm{T}_{\text {sol }}$ | Wave Solder Pb-Free | <2 to $3 \mathrm{sec} @ 260^{\circ} \mathrm{C}$ |  | 265 | ${ }^{\circ} \mathrm{C}$ |
| $\theta_{\text {JC }}$ | Thermal Resistance (Junction-to-Case) | (Note 2) | DFN8 | 35 to 40 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
2. JEDEC standard multilayer board - 2S2P (2 signal, 2 power)

Table 4. LVPECL DC CHARACTERISTICS $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V} ; \mathrm{V}_{\mathrm{EE}}=0.0 \mathrm{~V}$ (Note 3)

| Symbol | Characteristic | $-40^{\circ} \mathrm{C}$ |  |  | $25^{\circ} \mathrm{C}$ |  |  | $95^{\circ} \mathrm{C}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max |  |
| $\mathrm{I}_{\mathrm{EE}}$ | Power Supply Current |  | 24 | 28 |  | 24 | 28 |  | 25 | 30 | mA |
| $\mathrm{V}_{\mathrm{OH}}$ | Output HIGH Voltage (Note 4) | 2215 | 2295 | 2420 | 2275 | 2345 | 2420 | 2275 | 2345 | 2420 | mV |
| $\mathrm{V}_{\text {OL }}$ | Output LOW Voltage (Note 4) | 1470 | 1605 | 1745 | 1490 | 1595 | 1680 | 1490 | 1595 | 1680 | mV |
| $\mathrm{V}_{\mathrm{IH}}$ | Input HIGH Voltage (Single-Ended) | 2135 |  | 2420 | 2135 |  | 2420 | 2135 |  | 2420 | mV |
| $\mathrm{V}_{\mathrm{IL}}$ | Input LOW Voltage (Single-Ended) | 1490 |  | 1825 | 1490 |  | 1825 | 1490 |  | 1825 | mV |
| VIHCMR | Input HIGH Voltage Common Mode <br> Range (Differential) (Note 8) $\begin{gathered} \mathrm{V}_{\mathrm{pp}}<500 \mathrm{mV} \\ \mathrm{~V}_{\mathrm{pp}} \geqq 500 \mathrm{mV} \end{gathered}$ | $\begin{aligned} & 1.2 \\ & 1.4 \end{aligned}$ |  | $\begin{aligned} & 3.1 \\ & 3.1 \end{aligned}$ | $\begin{aligned} & 1.1 \\ & 1.3 \end{aligned}$ |  | $\begin{aligned} & 3.1 \\ & 3.1 \end{aligned}$ | $\begin{aligned} & 1.1 \\ & 1.3 \end{aligned}$ |  | $\begin{aligned} & 3.1 \\ & 3.1 \end{aligned}$ | $\begin{aligned} & \mathrm{V} \\ & \mathrm{~V} \end{aligned}$ |
| $\mathrm{IIH}^{\text {H }}$ | Input HIGH Current |  |  | 150 |  |  | 150 |  |  | 150 | $\mu \mathrm{A}$ |
| IIL | Input LOW Current D <br>  D | $\begin{gathered} \hline 0.5 \\ -600 \end{gathered}$ |  |  | $\begin{gathered} \hline 0.5 \\ -600 \end{gathered}$ |  |  | $\begin{gathered} \hline 0.5 \\ -600 \end{gathered}$ |  |  | $\mu \mathrm{A}$ $\mu \mathrm{A}$ |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 Ifpm.
3. Input and output parameters vary $1: 1$ with $\mathrm{V}_{\mathrm{CC}}$. $\mathrm{V}_{\mathrm{EE}}$ can vary $\pm 0.3 \mathrm{~V}$.
4. Outputs are terminated through a $50 \Omega$ resistor to $\mathrm{V}_{\mathrm{CC}}-2.0 \mathrm{~V}$.
5. $V_{I H C M R}$ min varies $1: 1$ with $V_{E E}$, max varies $1: 1$ with $V_{C C}$. The $V_{I H C M R}$ range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between $\mathrm{V}_{\mathrm{PP}}$ min and 1.0 V .

Table 5. LVNECL DC CHARACTERISTICS $\mathrm{V}_{\mathrm{CC}}=0.0 \mathrm{~V} ; \mathrm{V}_{\mathrm{EE}}=-3.3 \mathrm{~V}$ (Note 6)

| Symbol | Characteristic | -40 ${ }^{\circ} \mathrm{C}$ |  |  | $25^{\circ} \mathrm{C}$ |  |  | $95^{\circ} \mathrm{C}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max |  |
| $\mathrm{I}_{\text {EE }}$ | Power Supply Current |  | 24 | 28 |  | 24 | 28 |  | 25 | 30 | mA |
| $\mathrm{V}_{\mathrm{OH}}$ | Output HIGH Voltage (Note 7) | -1085 | -1005 | -880 | -1025 | -955 | -880 | -1025 | -955 | -880 | mV |
| $\mathrm{V}_{\mathrm{OL}}$ | Output LOW Voltage (Note 7) | -1830 | -1695 | -1555 | -1810 | -1705 | -1620 | -1810 | -1705 | -1620 | mV |
| $\mathrm{V}_{\mathrm{IH}}$ | Input HIGH Voltage (Single-Ended) | -1165 |  | -880 | -1165 |  | -880 | -1165 |  | -880 | mV |
| $\mathrm{V}_{\text {IL }}$ | Input LOW Voltage (Single-Ended) | -1810 |  | -1475 | -1810 |  | -1475 | -1810 |  | -1475 | mV |
| $\mathrm{V}_{\text {IHCMR }}$ | Input HIGH Voltage Common Mode Range (Differential) (Note 8) $\begin{gathered} \mathrm{V}_{\mathrm{pp}}<500 \mathrm{mV} \\ \mathrm{~V}_{\mathrm{pp}} \geqq 500 \mathrm{mV} \end{gathered}$ | $\begin{aligned} & -2.1 \\ & -1.9 \end{aligned}$ |  | $\begin{aligned} & -0.2 \\ & -0.2 \end{aligned}$ | $\begin{aligned} & -2.2 \\ & -2.0 \end{aligned}$ |  | $\begin{aligned} & -0.2 \\ & -0.2 \end{aligned}$ | $\begin{aligned} & -2.2 \\ & -2.0 \end{aligned}$ |  | $\begin{aligned} & -0.2 \\ & -0.2 \end{aligned}$ | $\begin{aligned} & \mathrm{V} \\ & \mathrm{v} \end{aligned}$ |
| $\mathrm{I}_{\mathrm{IH}}$ | Input HIGH Current |  |  | 150 |  |  | 150 |  |  | 150 | $\mu \mathrm{A}$ |
| IIL | $\begin{array}{ll}\text { Input LOW Current } & \text { D } \\ & \text { D }\end{array}$ | $\begin{gathered} \hline 0.5 \\ -600 \end{gathered}$ |  |  | $\begin{gathered} \hline 0.5 \\ -600 \end{gathered}$ |  |  | $\begin{gathered} \hline 0.5 \\ -600 \end{gathered}$ |  |  | $\mu \mathrm{A}$ $\mu \mathrm{A}$ |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 Ifpm.
6. Input and output parameters vary $1: 1$ with $\mathrm{V}_{\mathrm{CC}} . \mathrm{V}_{\mathrm{EE}}$ can vary $\pm 0.3 \mathrm{~V}$.
7. Outputs are terminated through a $50 \Omega$ resistor to $\mathrm{V}_{C C}-2.0 \mathrm{~V}$.
8. $\mathrm{V}_{\text {IHCMR }}$ min varies $1: 1$ with $\mathrm{V}_{\text {EE }}$, max varies $1: 1$ with $\mathrm{V}_{\mathrm{CC}}$. The $\mathrm{V}_{\text {IHCMR }}$ range is referenced to the most positive side of the differential input signal. Normal operation is obtained if the HIGH level falls within the specified range and the peak-to-peak voltage lies between VPPmin and 1.0 V .

## MC100LVEL11

Table 6. AC CHARACTERISTICS $\mathrm{V}_{\mathrm{CC}}=3.3 \mathrm{~V} ; \mathrm{V}_{\mathrm{EE}}=0.0 \mathrm{~V}$ or $\mathrm{V}_{\mathrm{CC}}=0.0 \mathrm{~V} ; \mathrm{V}_{\mathrm{EE}}=-3.3 \mathrm{~V}$ (Note 9 )

| Symbol | Characteristic | $-40^{\circ} \mathrm{C}$ |  |  | $25^{\circ} \mathrm{C}$ |  |  | $95^{\circ} \mathrm{C}$ |  |  | Unit |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  |  | Min | Typ | Max | Min | Typ | Max | Min | Typ | Max |  |
| $\mathrm{f}_{\text {max }}$ | Maximum Toggle Frequency |  |  |  |  | 1.0 |  |  |  |  | GHz |
| $\begin{aligned} & \text { tpLH } \\ & \text { tpHL } \end{aligned}$ | Propagation Delay to Output | 235 |  | 385 | 255 | 330 | 405 | 285 |  | 435 | ps |
| tSKEW | Within-Device Skew (Note 10) Device-to-Device (Note 11) Duty Cycle Skew (Note 12) |  | $\begin{gathered} \hline 5 \\ 10 \end{gathered}$ | $\begin{gathered} \hline 20 \\ 150 \\ 20 \end{gathered}$ |  | $\begin{gathered} 5 \\ 10 \end{gathered}$ | $\begin{gathered} \hline 20 \\ 150 \\ 20 \end{gathered}$ |  | $\begin{gathered} 5 \\ 10 \end{gathered}$ | $\begin{gathered} \hline 20 \\ 150 \\ 20 \end{gathered}$ | ps |
| $\mathrm{t}_{\text {IITTER }}$ | Random Clock Jitter (RMS) |  |  |  |  | 0.6 |  |  |  |  | ps |
| $\mathrm{V}_{\mathrm{PP}}$ | Input Swing (Note 13) | 200 |  | 1000 | 200 |  | 1000 | 200 |  | 1000 | mV |
| $\begin{aligned} & \mathrm{t}_{\mathrm{r}} \\ & \mathrm{t}_{\mathrm{f}} \end{aligned}$ | $\begin{aligned} & \text { Output Rise/Fall Times Q } \\ & (20 \%-80 \%) \end{aligned}$ | 120 |  | 320 | 120 | 220 | 320 | 120 |  | 320 | ps |

NOTE: Device will meet the specifications after thermal equilibrium has been established when mounted in a test socket or printed circuit board with maintained transverse airflow greater than 500 lfpm.
9. $\mathrm{V}_{\mathrm{EE}}$ can vary $\pm 0.3 \mathrm{~V}$.
10. Within-device skew defined as identical transitions on similar paths through a device.
11. Device-to-device skew for identical transitions at identical $\mathrm{V}_{\mathrm{CC}}$ levels.
12. Duty cycle skew is the difference between a $t_{P L H}$ and $t_{P H L}$ propagation delay through a device.
13. $\mathrm{V}_{\mathrm{PP}}(\mathrm{min})$ is the minimum input swing for which AC parameters guaranteed. The device will function properly with input swings below 200 mV , however, AC delays may move outside of the specified range. The device has a DC gain of $\approx 40$.


Figure 2. Output Swing versus Frequency

ORDERING INFORMATION

| Device | Package | Shipping ${ }^{\dagger}$ |
| :--- | :--- | :---: |
| MC100LVEL11DG | SOIC-8 <br> (Pb-Free) | 98 Units / Rail |
| MC100LVEL11DR2G | SOIC-8 <br> (Pb-Free) | $2500 /$ Tape \& Reel |
| MC100LVEL11DTG | TSSOP-8 <br> (Pb-Free) | 100 Units / Rail |
| MC100LVEL11DTR2G | TSSOP-8 <br> (Pb-Free) | $2500 /$ Tape \& Reel |
| MC100LVEL11MNR4G | DFN8 <br> (Pb-Free) | $1000 /$ Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
Resource Reference of Application Notes
AN1405/D - ECL Clock Distribution Techniques
AN1406/D - Designing with PECL (ECL at +5.0 V)
AN1503/D - ECLinPS $^{m}$ I/O SPiCE Modeling Kit
AN1504/D - Metastability and the ECLinPS Family $^{\text {AN1568/D }}$ - Interfacing Between LVDS and ECL
AN1672/D - The ECL Translator Guide
AND8001/D - Odd Number Counters Design
AND8002/D - Marking and Date Codes
AND8020/D - Termination of ECL Logic Devices
AND8066/D - Interfacing with ECLinPS
AND8090/D - AC Characteristics of ECL Devices

DFN8 2x2, 0.5P
CASE 506AA-01
ISSUE E
DATE 22 JAN 2010

## SCALE 4:1



NOTES:
. Dimensioning and tolerancing per ASME Y14.5M, 1994
CONTROLLING DIMENSION: MILLIMETERS.
2. CIMENSION B APPLIES TO PLATED

TERMINAL AND IS MEASURED BETWEEN
0.15 AND 0.20 MM FROM TERMINAL TIP.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

|  | MILLIMETERS |  |
| :---: | :---: | :---: |
| DIM | MIN | MAX |
| A | 0.80 | 1.00 |
| A1 | 0.00 | 0.05 |
| A3 | 0.20 REF |  |
| b | 0.20 | 10.30 |
| D | 2.00 BSC |  |
| D2 | 1.10 | 1.30 |
| E | 2.00 BS |  |
| E2 | 0.70 | 0.90 |
| e | 0.50 BSC |  |
| K | 0.30 REF |  |
| L | 0.25 | 0.35 |
| L1 | ---1 | 0.10 |

## GENERIC <br> MARKING DIAGRAM*

DETAIL B optional construction

BOTTOM VIEW



XX = Specific Device Code
M = Date Code

- = Pb-Free Device
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " $\mathrm{\nabla "}$, may or may not be present.

RECOMMENDED SOLDERING FOOTPRINT*

*For additional information on our Pb -Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | DFN8, 2.0X2.0, 0.5MM PITCH | PAGE 1 OF 1 |

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SOIC-8 NB
CASE 751-07
ISSUE AK
SCALE 1:1
DATE 16 FEB 2011


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. 751-01 THRU 751-06 ARE OBSOLETE. NEW
7. 751-01 THRU 751-06 AR
STANDARD IS 751-07.

| DIM | MILLIMETERS |  | INCHES |  |
| :---: | :---: | :---: | :---: | :---: |
|  | MIN | MAX | MIN | MAX |
|  | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC |  | 0.050 BSC |  |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0 | $0^{\circ}$ | $8^{\circ}$ | 0 |
|  | $\circ$ | 8 |  |  |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

## GENERIC

MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
= Year
$\begin{array}{ll}\mathrm{W} & =\text { Work Week } \\ \text { - } & =\text { Pb-Free Package }\end{array}$
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " $\mathrm{=}$ ", may or may not be present. Some products may not follow the Generic Marking.
*For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

## STYLES ON PAGE 2

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| ---: | :--- | :--- | :--- |
| DESCRIPTION: | SOIC-8 NB | PAGE 1 OF 2 |

[^0] rights of others.

SOIC-8 NB
CASE 751-07
ISSUE AK
DATE 16 FEB 2011

STYLE

| PIN 1. | EMITTER |
| ---: | :--- |
| 2. | COLLECTOR |
| 3. | COLLECTOR |
| 4. | EMITTER |
| 5. | EMITTER |
| 6. | BASE |
| 7. | BASE |
| 8. | EMITTER |
| STYLE 5: |  |
| PIN 1. | DRAIN |
| 2. | DRAIN |
| 3. | DRAIN |
| 4. | DRAIN |
| 5. | GATE |
| 6. | GATE |
| 7. | SOURCE |
| 8. | SOURCE |

STYLE 9:
PIN 1. EMITTER, COMMON
COLLECTOR, DIE \#1 COLLECTOR, DIE \#2 EMITTER, COMMON EMITTER, COMMON BASE, DIE \#2
BASE, DIE \#1
8. EMITTER, COMMON

STYLE 13:
PIN 1. N.C.
2. SOURCE
3. SOURCE

GATE
DRAIN
DRAIN
DRAIN
8. DRAIN

STYLE 17:
PIN 1. VCC
V2OUT
V10UT
V10UT
TXE
RXE
VEE
7. GND
8. ACC

STYLE 21:
PIN 1. CATHODE 1
2. CATHODE 2
3. CATHODE 3

CATHODE 4
CATHODE 5
6. COMMON ANODE
7. COMMON ANODE
8. CATHODE 6

STYLE 25:
PIN 1. VIN
2. $\mathrm{N} / \mathrm{C}$

REXT
GND
IOUT
IOUT
IOUT
8. IOUT

## STYLE 29

PIN 1. BASE, DIE \#
EMITTER, \#1
BASE, \#2
. EMITTER, \#2
5. COLLECTOR, \#2
6. COLLECTOR, \#2
7. COLLECTOR, \#1
8. COLLECTOR, \#1

STYLE
PIN 1. COLIECTOR,
2. COLLECTOR, \#
3. COLLECTOR, \#2

COLLECTOR, \#2
BASE, \#2
. EMITTER, \#2
7. BASE, \#1
8. EMITTER, \#1

STYLE 6:
PIN 1. SOURCE
DRAIN
3. DRAIN
4. SOURCE

SOURCE
6. GATE
7. GATE
8. SOURCE

STYLE 10:
PIN 1. GROUND
2. BIAS 1
3. OUTPUT

GROUND
GROUND
BIAS 2
7. INPUT
8. GROUND

STYLE 14
PIN 1. N-SOURCE
2. N-GATE
. P-SOURCE
P-GATE
5.DRAIN
6. P-DRAIN
7. N-DRAIN
8. N -DRAIN

STYLE 18
PIN 1. ANODE
2. ANODE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. CATHODE
8. CATHODE

STYLE 22 :
PIN 1. I/O LINE
2. COMMON CATHODE/VCC
3. COMMON CATHODE/VCC
4. I/O LINE 3
5. COMMON ANODE/GND
6. I/O LINE 4
7. I/O LINE 5
8. COMMON ANODE/GND

STYLE 26:
PIN 1. GND
2. $\mathrm{dv} / \mathrm{dt}$
3. ENABLE
4. ILIMIT

SOURCE
SOURCE
SOURCE
8. VCC

STYLE 30:
PIN 1. DRAIN 1
2. DRAIN 1
. GATE 2
4. SOURCE 2
5. SOURCE 1/DRAIN 2
. SOURCE 1/DRAIN 2
SOURCE 1/DRAIN 2
8. GATE 1

STYLE 3
STYLE
2. DRAIN, DIE
2. DRAIN, \#1
2. DRAIN, \#
3. DRAIN, \#2
4. DRAIN, \#2
5. GATE, \#2
7. GATE, \#1
8. SOURCE, \#1

## STYLE 7

PIN 1. INPUT
2. EXTERNAL BYPASS
3. THIRD STAGE SOURCE
4. GROUND
5. DRAIN
6. GATE 3
7. SECOND STAGE Vd
8. FIRST STAGE Vd

## STYLE 11:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

## STYLE 15:

PIN 1. ANODE 1
2. ANODE 1
3. ANODE 1
4. ANODE 1
5. CATHODE, COMMON
6. CATHODE, COMMON
7. CATHODE, COMMON
8. CATHODE, COMMON

## STYLE 19:

PIN 1. SOURCE
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN
6. MIRROR 2
7. DRAIN 1
8. MIRROR 1

## STYLE 23:

PIN 1. LINE 1 IN
2. COMMON ANODE/GND
3. COMMON ANODE/GND
4. LINE 2 IN
5. LINE 2 OUT
6. COMMON ANODE/GND
7. COMMON ANODE/GND
8. LINE 1 OUT

STYLE 27:
PIN 1. ILIMIT
2. OVLO
3. UVLO
4. INPUT+
5. INPUT+
5. SOURCE
6. SOURCE
7. SOURCE
8. DRAIN

STYLE 4:
PIN 1. ANODE
2. ANODE
3. ANODE
4. ANODE
5. ANODE
6. ANODE
8. COMMON CATHODE

## STYLE 8:

PIN 1. COLLECTOR, DIE \#1
2. BASE, \#1
3. BASE, \#2
4. COLLECTOR, \#2
5. COLLECTOR, \#2
6. EMITTER, \#2
7. EMITTER, \#1
8. COLLECTOR, \#1

## STYLE 12

PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

## STYLE 16:

PIN 1. EMITTER, DIE \#1
2. BASE, DIE \#1
3. EMITTER, DIE \#2
3. EMITTER, DIE
4. BASE, DIE \#2
4. BASE, DIE \#2
6. COLLECTOR, DIE \#2
7. COLLECTOR, DIE \#1
8. COLLECTOR, DIE \#1

## STYLE 20:

PIN 1. SOURCE (N)
2. GATE (N)
3. SOURCE (P)
4. GATE (P)
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 24
PIN 1. BASE
2. EMITTER
3. COLLECTOR/ANODE
4. COLLECTOR/ANODE
5. CATHODE
6. CATHODE
7. COLLECTOR/ANODE
8. COLLECTOR/ANODE

## STYLE 28:

PIN 1. SW_TO_GND
2. DASIC $\bar{O} F F$
3. DASIC_SW_DET
4. GND
5. V_MON
6. VBULK
7. VBULK
8. VIN

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TSSOP 8

## CASE 948R-02

ISSUE A
DATE 04/07/2000

## SCALE 2:1


notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PROTRUSI
PER SIDE
5. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY
6. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

|  | MILLIMETERS |  | INCHES |  |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| DIM | MIN | MAX | MIN | MAX |  |  |
| A | 2.90 | 3.10 | 0.114 | 0.122 |  |  |
| B | 2.90 | 3.10 | 0.114 | 0.122 |  |  |
| C | 0.80 | 1.10 | 0.031 | 0.043 |  |  |
| D | 0.05 | 0.15 | 0.002 | 0.006 |  |  |
| F | 0.40 | 0.70 | 0.016 | 0.028 |  |  |
| G | 0.65 BSC |  | 0.026 BSC |  |  |  |
| K | 0.25 |  | 0.40 | 0.010 |  | 0.016 |
| L | 4.90 BSC |  | 0.193 BSC |  |  |  |
| M | $0^{\circ}$ |  | $6^{\circ}$ | $0^{\circ}$ |  | $6^{\circ}$ |


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